

TOSHIBA INSULATED GATE BIPOLAR TRANSISTOR SILICON N CHANNEL IGBT

# GT10J303

HIGH POWER SWITCHING APPLICATIONS

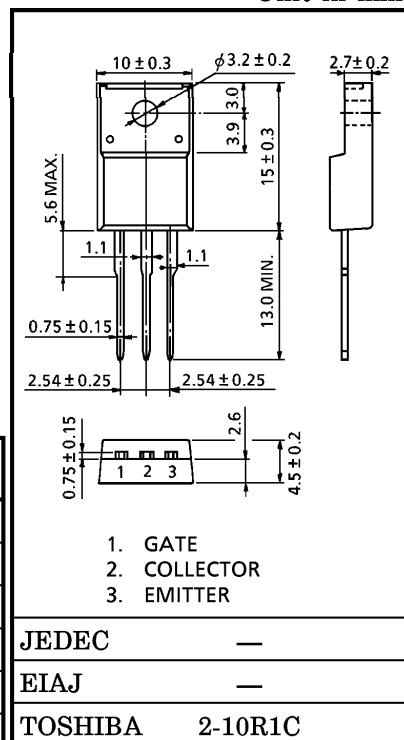
MOTOR CONTROL APPLICATIONS

Unit in mm

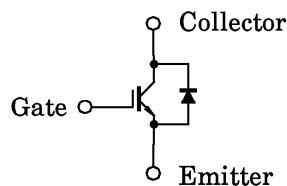
- The 3rd Generation.
- Enhancement-Mode.
- High Speed. :  $t_f = 0.30 \mu s$  (Max.) ( $I_C = 10A$ )
- Low Saturation Voltage. :  $V_{CE(sat)} = 2.7V$  (Max.) ( $I_C = 10A$ )
- FRD included between Emitter and Collector.

MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Emitter Voltage		$V_{CES}$	600	V
Gate-Emitter Voltage		$V_{GES}$	$\pm 20$	V
Collector Current	DC	$I_C$	10	A
	1ms	$I_{CP}$	20	A
Emitter-Collector Forward Current	DC	$I_F$	10	A
	1ms	$I_{FM}$	20	A
Collector Power Dissipation ( $T_c = 25^\circ C$ )		$P_C$	30	W
Junction Temperature		$T_j$	150	$^\circ C$
Storage Temperature Range		$T_{stg}$	$-55 \sim 150$	$^\circ C$



EQUIVALENT CIRCUIT



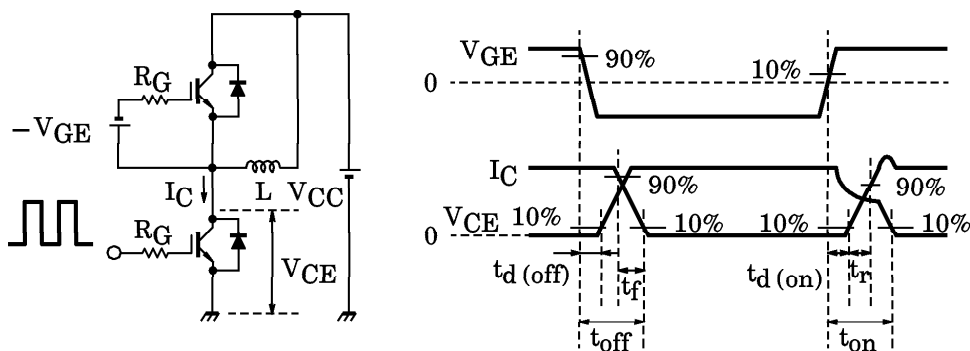
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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	$I_{GES}$	$V_{GE} = \pm 20V, V_{CE} = 0$	—	—	$\pm 500$	nA
Collector Cut-Off Current	$I_{CES}$	$V_{CE} = 600V, V_{GE} = 0$	—	—	1.0	mA
Gate-Emitter Cut-Off Voltage	$V_{GE(OFF)}$	$I_C = 1mA, V_{CE} = 5V$	5.0	—	8.0	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10A, V_{GE} = 15V$	—	2.1	2.7	V
Input Capacitance	$C_{ies}$	$V_{CE} = 20V, V_{GE} = 0, f = 1MHz$	—	720	—	pF
Switching Time	Rise Time	Inductive Load $V_{CC} = 300V, I_C = 10A$ $V_{GG} = \pm 15V, R_G = 100\Omega$ (Note 1)	—	0.12	—	$\mu s$
	Turn-On Time		—	0.40	—	
	Fall Time		—	0.15	0.30	
	Turn-Off Time		—	0.50	—	
Peak Forward Voltage	$V_F$	$I_F = 10A, V_{GE} = 0$	—	—	2.0	V
Reverse Recovery Time	$t_{rr}$	$I_F = 10A, di/dt = -100A/\mu s$	—	—	200	ns
Thermal Resistance (IGBT)	$R_{th(j-c)}$	—	—	—	4.17	°C/W
Thermal Resistance (Diode)	$R_{th(j-c)}$	—	—	—	4.9	°C/W

(Note 1) Switching time measurement circuit and input/output waveforms



Switching loss measurement waveforms

